

# SOT223 PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

## FZT788B

ISSUE 3 - OCTOBER 1995

### FEATURES

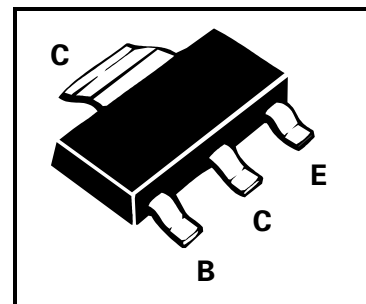
- \* Low equivalent on-resistance;  $R_{CE(sat)} 93m\Omega$  at 3A
- \* Gain of 300 at  $I_C=2$  Amps and Very low saturation voltage

### APPLICATIONS

- \* Battery powered circuits

COMPLEMENTARY TYPE – FZT688B

PARTMARKING DETAIL – FZT788B



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-15	V
Collector-Emitter Voltage	$V_{CEO}$	-15	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-8	A
Continuous Collector Current	$I_C$	-3	A
Power Dissipation at $T_{amb}=25^\circ C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^\circ C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-15			V	$I_C=-100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-15			V	$I_C=-10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB}=-10V$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB}=-4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.15 -0.25 -0.45 -0.5	V	$I_C=-0.5A, I_B=-2.5mA^*$ $I_C=-1A, I_B=-5mA^*$ $I_C=-2A, I_B=-10mA^*$ $I_C=-3A, I_B=-50mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.9	V	$I_C=-1A, I_B=-5mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C=-1A, V_{CE}=-2V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	500 400 300 150		1500		$I_C=-10mA, V_{CE}=-2V^*$ $I_C=-1A, V_{CE}=-2V^*$ $I_C=-2A, V_{CE}=-2V^*$ $I_C=-6A, V_{CE}=-2V^*$
Transition Frequency	$f_T$	100			MHz	$I_C=-50mA, V_{CE}=-5V$ $f=50MHz$
Input Capacitance	$C_{ibo}$		225		pF	$V_{EB}=-0.5V, f=1MHz$
Output Capacitance	$C_{obo}$		25		pF	$V_{CB}=-10V, f=1MHz$
Switching Times	$t_{on}$ $t_{off}$		35 400		ns ns	$I_C=-500mA, I_{B1}=-50mA$ $I_{B2}=-50mA, V_{CC}=-10V$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$   
Spice parameter data is available upon request for this device

# FZT788B

## TYPICAL CHARACTERISTICS

